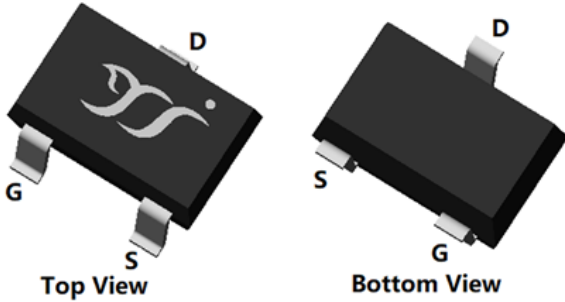
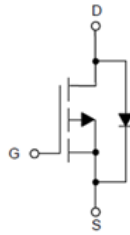


P-Channel Enhancement Mode Field Effect Transistor



SOT-323



Product Summary

- V_{DS} -60 V
- I_D -0.17 A
- $R_{DS(ON)}$ (at $V_{GS}=-10V$) 8 ohm
- $R_{DS(ON)}$ (at $V_{GS}=-4.5V$) 9.9 ohm

General Description

- Trench Power LV MOSFET technology
- Low $R_{DS(ON)}$
- Low Gate Charge
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- Video monitor
- Power management

■ Absolute Maximum Ratings ($T_A=25$ unless otherwise noted)

Parameter	Symbol	Maximum	Unit
Drain-source Voltage	V_{DS}	-60	V
Gate-source Voltage	V_{GS}	20	V
Drain Current	I_D	$T_A=25$ @ Steady State	-0.17
		$T_A=70$ @ Steady State	-0.14
Pulsed Drain Current ^A	I_{DM}	-0.68	A
Total Power Dissipation @ $T_A=25$	P_D	0.15	W
Thermal Resistance Junction-to-Ambient ^B	$R_{\theta JA}$	833	W
Junction and Storage Temperature Range	T_J, T_{STG}	-55 +150	

■ Ordering Information

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
BSS84W	F2	B84.	3000	30000	120000	7" reel



BSS84W

■ Electrical Characteristics (T_J=25 unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D =-250μA	-60			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-60V, V _{GS} =0V			-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} = 20V, V _{DS} =0V			100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D =-250μA	-0.9	-1.4	-2.0	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = -10V, I _D =-0.15A		3.3	8	Ω
		V _{GS} = -4.5V, I _D =-0.15A		3.5	9.9	
Diode Forward Voltage	V _{SD}	I _S =-0.17A, V _{GS} =0V			-1.2	V
Maximum Body-Diode Continuous Current	I _S				-0.17	A
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =-30V, V _{GS} =0V, f=1MHZ		43		pF
Output Capacitance	C _{oss}			2.9		
Reverse Transfer Capacitance	C _{rss}			1.8		
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =-10V, V _{DS} =-30V, I _D =-0.15 A		1.77		nC
Gate Source Charge	Q _{gs}			0.57		
Gate Drain Charge	Q _{gd}			0.18		
Reverse Recovery Charge	Q _{rr}	I _F =-0.15A, di/dt=100A/μs		13		
Reverse Recovery Time	t _{rr}			23		
Turn-on Delay Time	t _{D(on)}	V _{GS} =-4.5V, V _{DD} =-30V, I _D =-0.15A, R _{GEN} =2.5Ω		8.6		ns
Turn-on Rise Time	t _r			20		
Turn-off Delay Time	t _{D(off)}			15		
Turn-off Fall Time	t _f			77		

A. Pulse Test: Pulse Width 10us, Duty cycle 2%.

B. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.



■ Typical Performance Characteristics

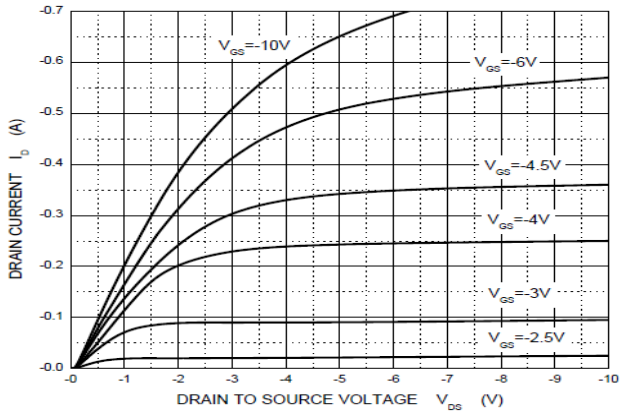


Figure1. Output Characteristics

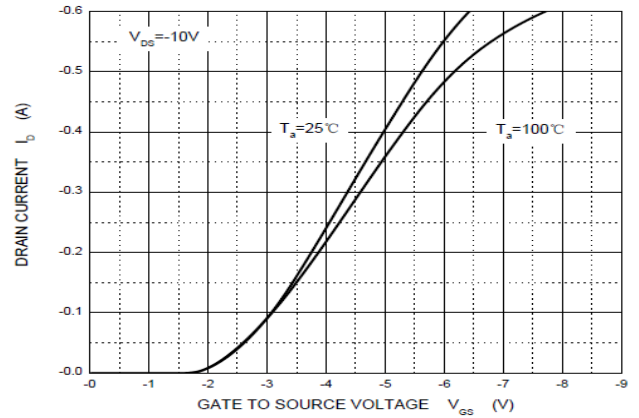


Figure2. Transfer Characteristics

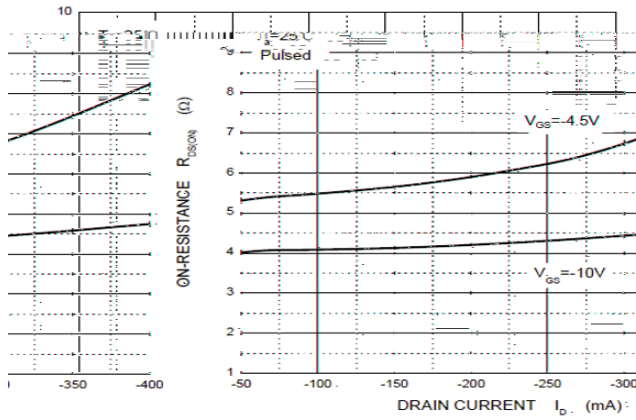


Figure3. Drain-Source on Resistance

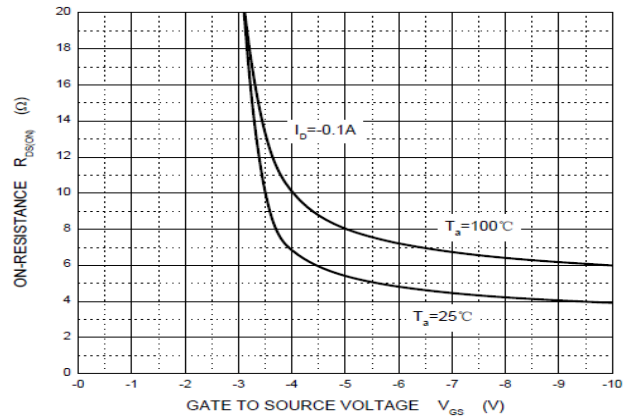


Figure4. Drain-Source on Resistance

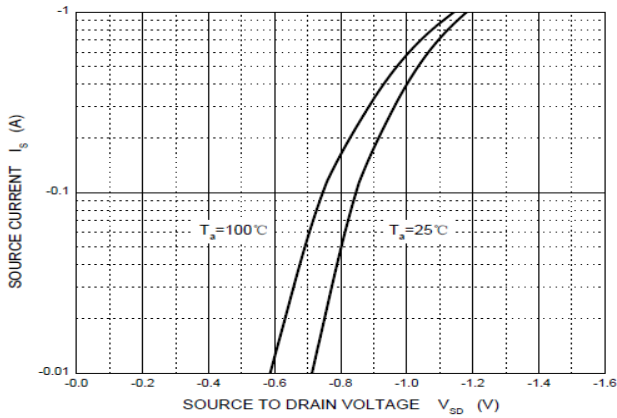


Figure5. Diode Forward Voltage vs. current

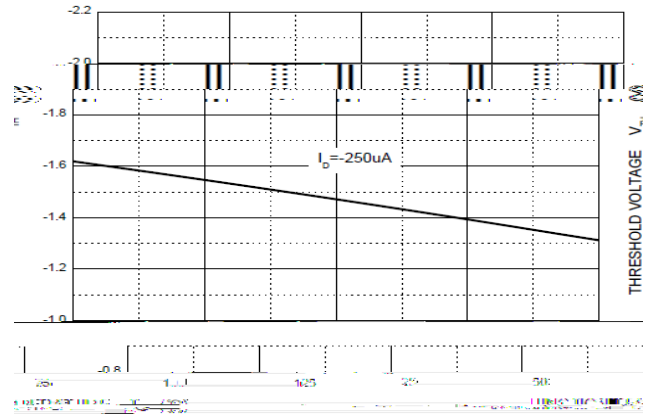


Figure6. Gate Threshold vs. Junction Temperature



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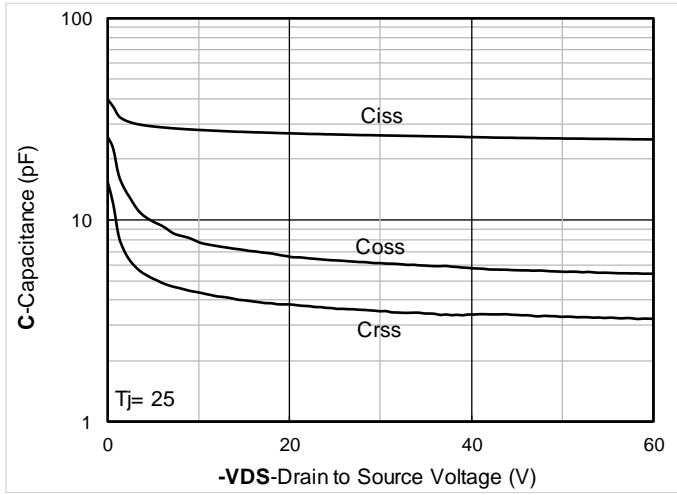


Figure7. Capacitance Characteristics

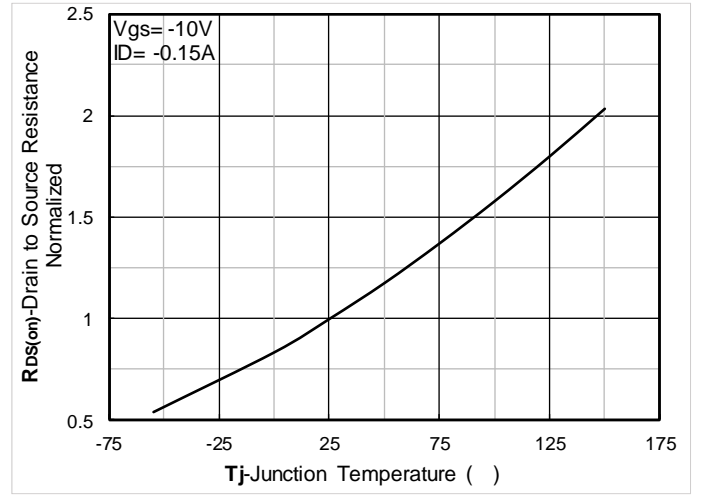
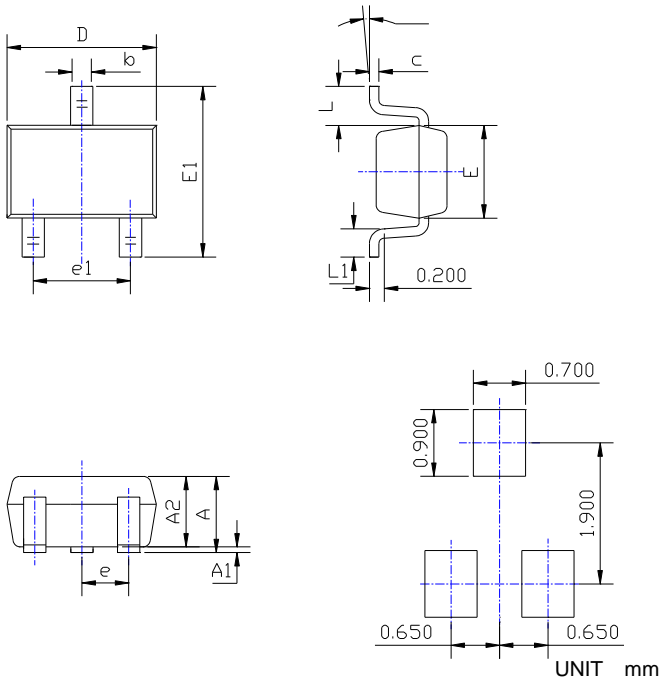


Figure8. Normalized On-Resistance



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■ SOT-323 Package Information



SYMBOL	DIMENSIONS			
	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.035	0.043	0.900	1.100
A1	0.000	0.004	0.000	0.100
A2	0.035	0.039	0.900	1.000
b	0.006	0.016	0.150	0.400
c	0.004	0.010	0.100	0.250
D	0.071	0.087	1.800	2.200
E	0.045	0.053	1.150	1.350
E1	0.085	0.096	2.150	2.450
e	0.026 TYP		0.650 TYP	
e1	0.047	0.055	1.200	1.400
L	0.021 REF		0.525 REF	
L1	0.010	0.018	0.260	0.460
	0°	8°	0°	8°

- NOTE:
1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
2. TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
3. THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.



BSS84W

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